11. The process of claim 1, further comprising:
forming an anti-reflective coating over the dielectric stack, the anti-reflective coating together with the dielectric stack being configured to have a particular breakdown voltage.

12. The process of claim 11, wherein the anti-reflective coating comprises a layer of amorphous silicon and a layer of silicon nitride.

13. The process of claim 11, wherein the particular breakdown voltage is greater than $1x10^7$ V/cm.

14. The process of claim 11, wherein the particular breakdown voltage is configured by decreasing a refractive index of the interlayer dielectric to less than 1.95.

15. The process of claim 1,
wherein the dielectric stack has an optical property configured for a particular type of laser ablation.

16. The process of claim 15, wherein the particular type of laser ablation comprises indirect ablation.

17. The process of claim 16, wherein the dielectric stack has a refractive index less than 1.97 and the laser has a wavelength equal to or longer than 530 nm.

18. The process of claim 15, wherein the dielectric comprises doped silicon dioxide.

~~19. A solar cell fabricated using the process of claim 1.~~